

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S29	6	"6524935"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/22 13:06
S30	862	("SiGe" 'sige' silicon near3 geranium) with (strained relaxed)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/22 14:23
S31	632	S30 and (implant\$3 nitridation nitrify nitrification inject\$3 silicide silicidation)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 09:02
S32	632	S30 and (implant\$3 nitridation nitrify nitrification inject\$3 silicide silicidation oxynitridation)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 09:03
S33	175	S32 and ("SiGe" 'sige' silicon near3 geranium) with (crystalline ((mono single) near3 (crystal crystalline)))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 09:07
S34	166	S33 and ("SiGe" 'sige' silicon near3 geranium) with ('soi' insulat\$3 substrate)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 09:08
S35	166	S34 and (nitride silicon oxynitride nitrogen germanium metal metal\$4 heat\$3 anneal\$3 oxide)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 10:16
S37	1	S35 and vacan\$3	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 09:12
S38	95	S35 and \$4nitrid\$7	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 18:08
S39	10	"6455398"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 18:08

S40	1	10/765999	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/22 13:07
S41	1076	("SiGe" "GeSi" 'sige' 'gesi' silicon near3 germanium) with (strained strain relaxed relaxation)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/22 14:31
S42	1076	S41 and ("SiGe" "GeSi" 'sige' 'gesi' silicon near3 germanium strained strain relaxed relaxation)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/22 14:32
S43	37	S42 and strain\$3 near3 inducing	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/22 14:32

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	U	Document I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	2	3	
39	r	US 6677655	2004011	16	Silicon wafer with embed	257/432	257/186;		Fitzgerald; Eugene	F	r	r	r	r	r
40	r	US 6649480	2003111	24	Method of fabricating C	438/285	257/E21.6		Fitzgerald; Eugene	F	r	r	r	r	r
41	r	US 6642536	2003110	11	Hybrid silicon on insulat	257/19	257/20;		Xiang; Qi et al.	F	r	r	r	r	r
42	r	US 6633066	2003101	31	CMOS integrated circuit	257/347	257/348;		Bae; Geum-jong et	F	r	r	r	r	r
43	r	US 6607948	2003081	18	Method of manufacturing	438/151	438/938		Sugiyama; Naoharu	F	r	r	r	r	r
44	r	US 6603156	2003080	6	Strained silicon on insula	257/190	257/347;		Rim; Kern	F	r	r	r	r	r
45	r	US 6602613	2003080	14	Heterointegration of mate	428/641	117/953;		Fitzgerald; Eugene	F	r	r	r	r	r
46	r	US 6597016	2003072	26	Semiconductor device an	257/77	257/289;		Yuki; Koichiro et al	F	r	r	r	r	r
47	r	US 6593641	2003071	26	Relaxed silicon germaniu	257/616	257/18;		Fitzgerald; Eugene	F	r	r	r	r	r
48	r	US 6573126	2003060	13	Process for producing se	438/149	257/E21.5		Cheng; Zhi-Yuan et	F	r	r	r	r	r
49	r	US 6555839	2003042	20	Buried channel strained s	257/18	257/19;		Fitzgerald; Eugene	F	r	r	r	r	r
50	r	US 6521041	2003021	20	Etch stop layer system	117/94	117/915;		Wu; Kenneth C. et	F	r	r	r	r	r
51	r	US 6495402	2002121	8	Semiconductor-on-insula	438/149	257/E21.4		Yu; Bin et al.	F	r	r	r	r	r
52	r	US 6455871	2002092	10	SiGe MODFET with a m	257/12	257/189;		Shim; Kyu Hwan et	F	r	r	r	r	r
53	r	US 6410371	2002062	7	Method of fabrication of	438/151	257/E21.4		Yu; Bin et al.	F	r	r	r	r	r
54	r	US 6380590	2002043	7	SOI chip having multiple	257/350	257/289;		Yu; Bin	F	r	r	r	r	r
55	r	US 6350993	2002022	22	High speed composite p-c	257/19	257/18;		Chu; Jack Oon et al	F	r	r	r	r	r
56	r	US 6326667	2001120	13	Semiconductor devices a	257/347	257/18;		Sugiyama; Naoharu	F	r	r	r	r	r
57	r	US 6310367	2001103	32	MOS transistor having a f	257/190	257/19		Yagishita; Atsushi e	F	r	r	r	r	r

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